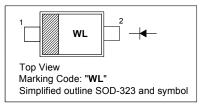
BAND SWITCHING DIODE

Features

- Very small plastic SMD package
- · Low diode capacitance
- · Low diode forward resistance
- · Small inductance

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Cathode |
| 2 | Anode |



Absolute Maximum Ratings (T_a = 25 °C)

| Parameter | Symbol | Value | Unit |
|--------------------------------------|------------------|---------------|------|
| Continuous Reverse Voltage | V_R | 35 | V |
| Continuous Forward Current | I _F | 100 | mA |
| Power Dissipation | P _{tot} | 500 | mW |
| Operating Junction Temperature Range | TJ | - 65 to + 150 | °C |
| Storage Temperature Range | Ts | - 65 to + 150 | °C |

Electrical Characteristics at T_a = 25 °C

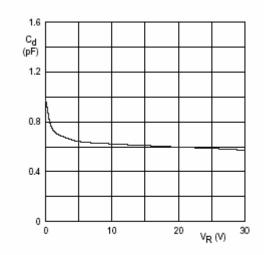
| Parameter | Symbol | Тур. | Max. | Unit |
|-------------------------------------------------------------------------------------------------------------------|------------------|------|-------------|------|
| Forward Voltage at I _F = 10 mA | V _F | - | 1 | V |
| Reverse Current at V _R = 20 V | I _R | - | 20 | nA |
| Diode Capacitance at $V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$ at $V_R = 3 \text{ V}$, $f = 1 \text{ MHz}$ | C _D | | 1.05 0.9 | pF |
| Diode Forward Resistance at I_F = 3 mA, f = 100 MHz at I_F = 10 mA, f = 100 MHz | r _D | - | 0.7 0.5 | Ω |
| Reverse Resistance at V _R = 1 V, f = 100 MHz | 1/g _p | 100 | - | ΚΩ |
| Series Inductance | Ls | 2 | - | nH |





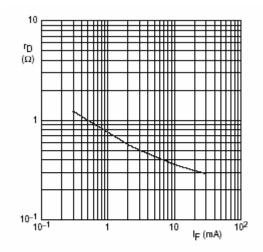


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f = 1 MHz; T_J = 25 °C.

Fig.2 Diode capacitance as a function of reverse voltage; typical values.



f = 100 MHz; T_j = 25 °C.

Diode forward resistance as a function of forward current; typical values.







Dated: 01/09/2006

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

